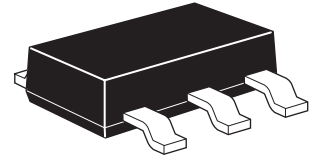


# ZXMN10A25G

## 100V SOT223 N-channel enhancement mode MOSFET

### Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.125 @ $V_{GS} = 10V$	4
	0.150 @ $V_{GS} = 6V$	3.7



### Description

This new generation trench MOSFET from Zetex features a unique structure which combines the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### Features

- Low on-resistance
- Fast switching speed
- Low gate drive
- SOT223 package

### Applications

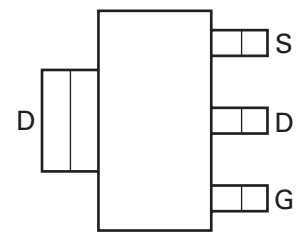
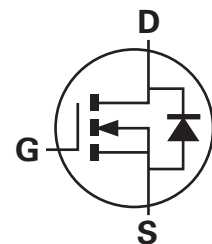
- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A25GTA	7	12	1,000

### Device marking

ZXMN  
10A25



Pinout - top view

# ZXMN10A25G

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	$V_{DSS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current @ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb} = 70^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(a)}$	$I_D$	4 3.2 2.9	A
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	17	A
Continuous source current (body diode) <sup>(b)</sup>	$I_S$	5.4	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	17	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	$P_D$	2	W
Linear derating factor		16	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	$P_D$	3.9	W
Linear derating factor		31	mW/ $^{\circ}C$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	32	$^{\circ}C/W$

### NOTES:

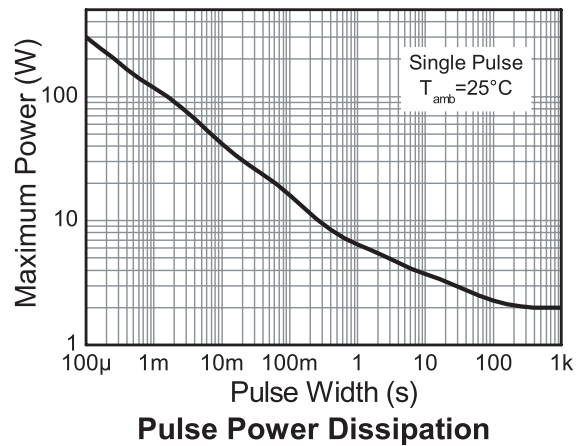
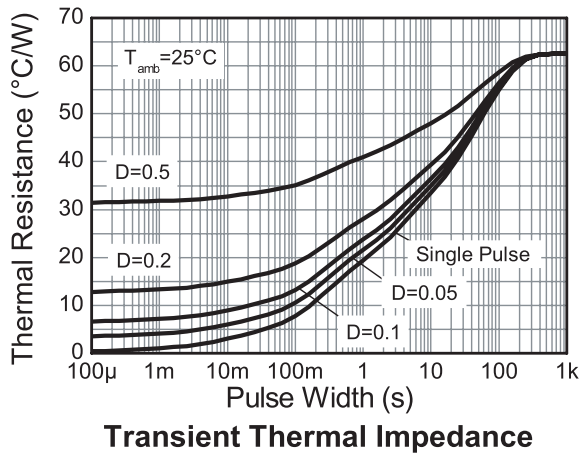
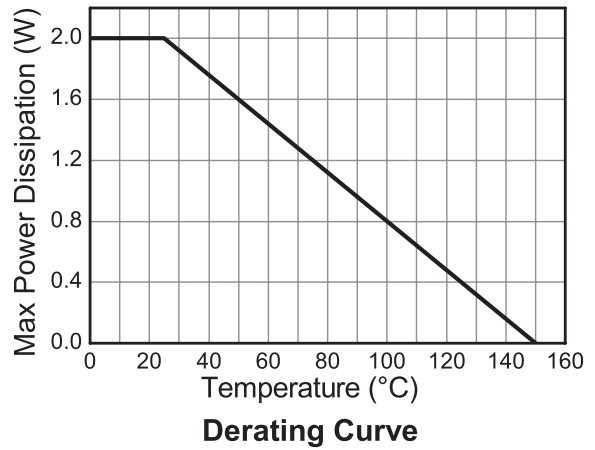
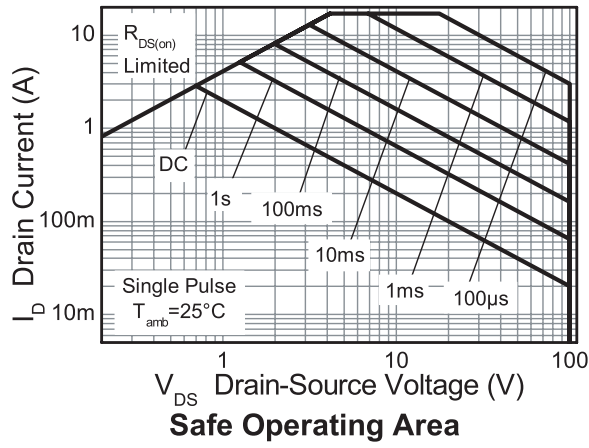
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB,  $D=0.02$ , pulse width  $\leq 300\mu s$  - pulse width limited by maximum junction temperature.

# ZXMN10A25G

## Thermal characteristics



# ZXMN10A25G

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	100			V	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero gate voltage drain current	$I_{DSS}$			0.5	$\mu\text{A}$	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$I_D = 250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance <sup>(*)</sup>	$R_{DS(on)}$			0.125	$\Omega$	$V_{GS} = 10\text{V}$ , $I_D = 2.9\text{A}$
				0.150	$\Omega$	$V_{GS} = 6\text{V}$ , $I_D = 2.6\text{A}$
Forward transconductance <sup>(*)(‡)</sup>	$g_{fs}$		7.3		S	$V_{DS} = 15\text{V}$ , $I_D = 2.9\text{A}$
<b>Dynamic<sup>(‡)</sup></b>						
Input capacitance	$C_{iss}$		859		pF	$V_{DS} = 50\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	$C_{oss}$		57		pF	
Reverse transfer capacitance	$C_{rss}$		33		pF	
<b>Switching<sup>(†) (‡)</sup></b>						
Turn-on-delay time	$t_{d(on)}$		4.9		ns	$V_{DD} = 50\text{V}$ , $I_D = 1\text{A}$ $R_G \approx 6.0\Omega$ , $V_{GS} = 10\text{V}$
Rise time	$t_r$		3.7		ns	
Turn-off delay time	$t_{d(off)}$		18		ns	
Fall time	$t_f$		9.4		ns	
Gate charge	$Q_g$		9.6		nC	$V_{DS} = 50\text{V}$ , $V_{GS} = 5\text{V}$ $I_D = 2.9\text{A}$
Total gate charge	$Q_g$		17		nC	$V_{DS} = 50\text{V}$ , $V_{GS} = 10\text{V}$ $I_D = 2.9\text{A}$
Gate-source charge	$Q_{gs}$		3.8		nC	
Gate drain charge	$Q_{gd}$		5.4		nC	
<b>Source-drain diode</b>						
Diode forward voltage <sup>(*)</sup>	$V_{SD}$		0.85	0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = 4\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time <sup>(‡)</sup>	$t_{rr}$		40.5		ns	$T_j = 25^{\circ}\text{C}$ , $I_S = 2.9\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge <sup>(‡)</sup>	$Q_{rr}$		62		nC	

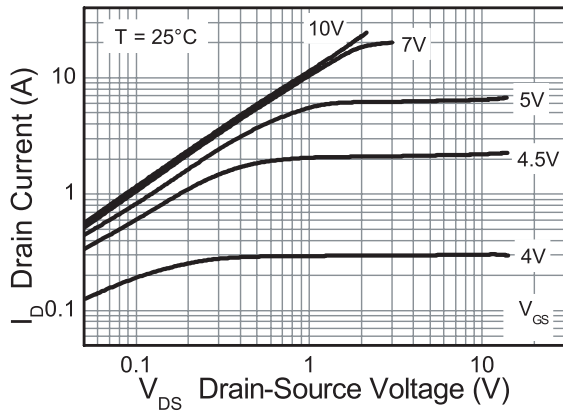
### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

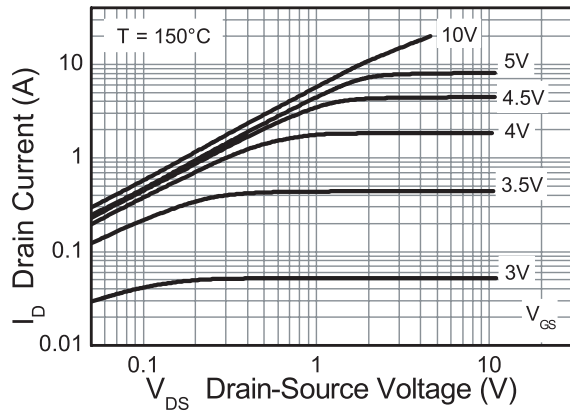
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

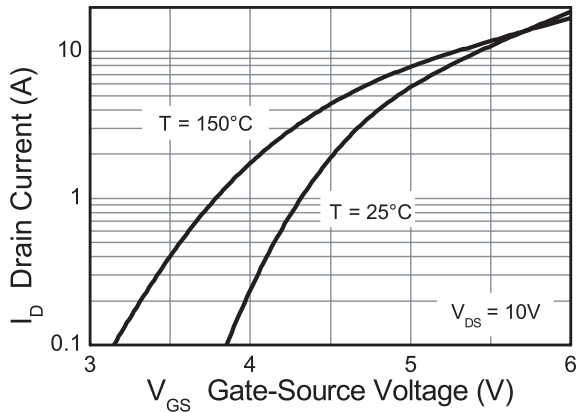
## Typical Characteristics



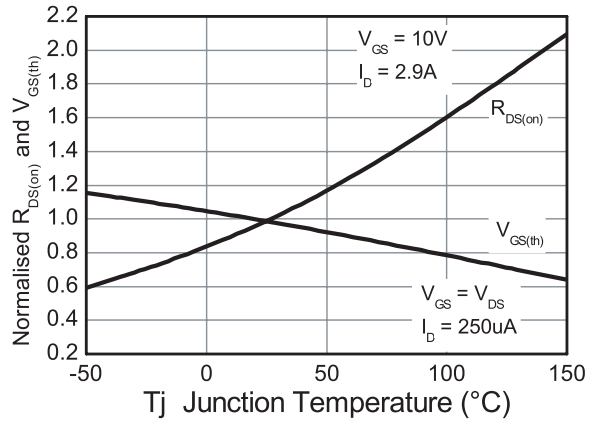
Output Characteristics



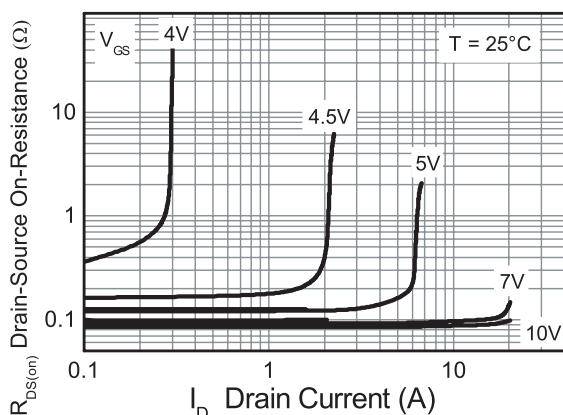
Output Characteristics



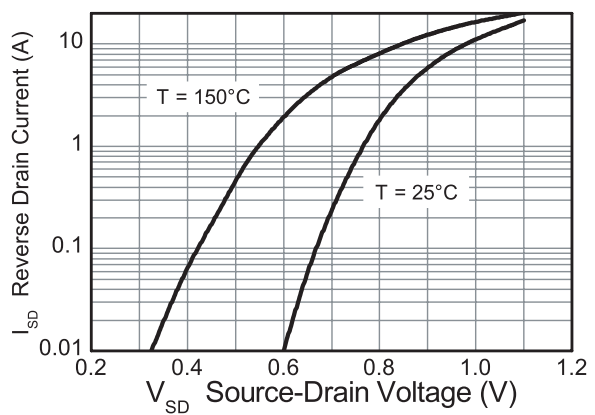
Typical Transfer Characteristics



Normalised Curves v Temperature

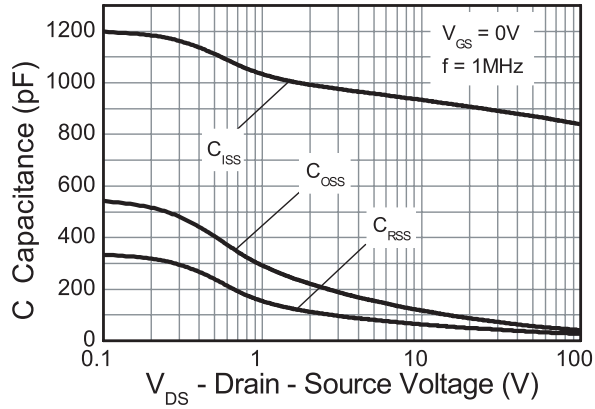


On-Resistance v Drain Current

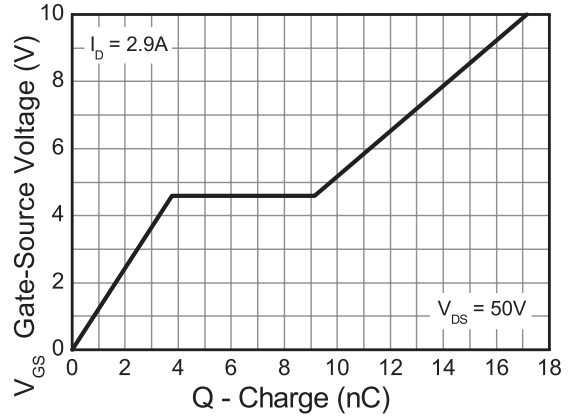


Source-Drain Diode Forward Voltage

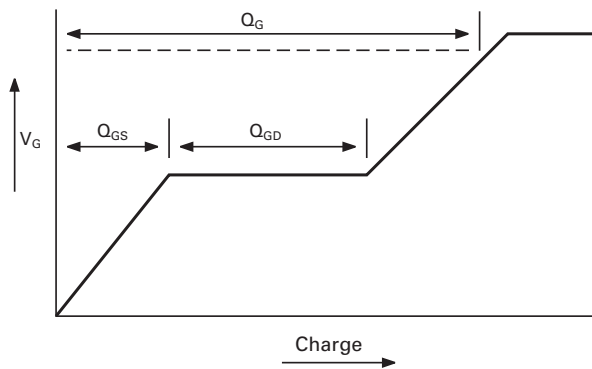
## Typical Characteristics



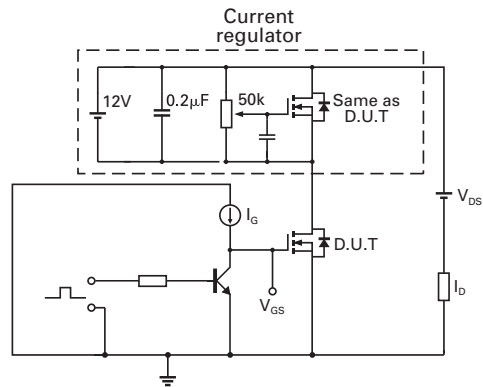
Capacitance v Drain-Source Voltage



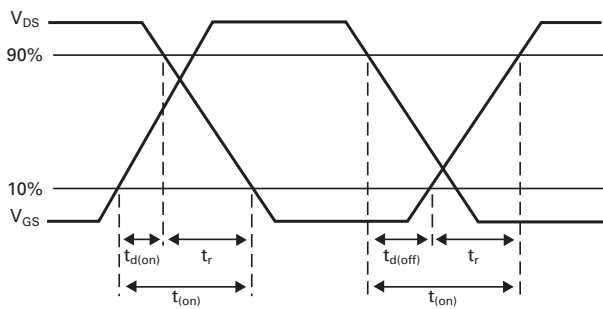
Gate-Source Voltage v Gate Charge



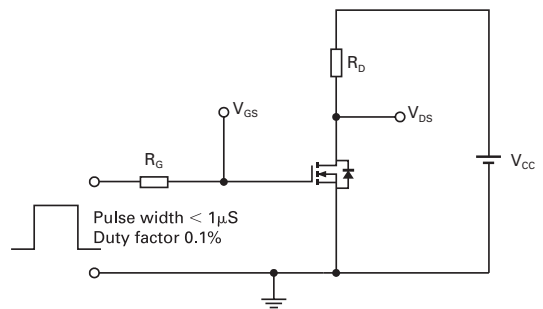
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



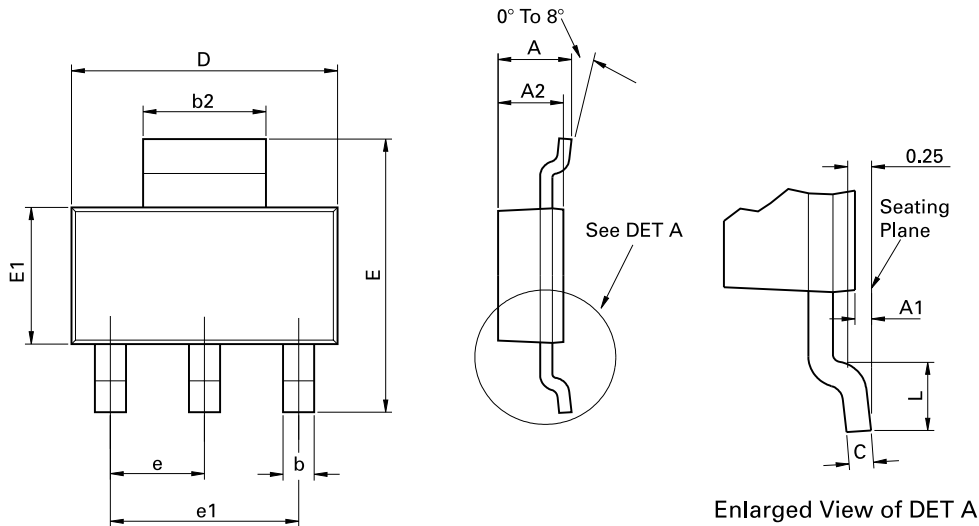
Switching time test circuit

# ZXMN10A25G

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# ZXMN10A25G

## Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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